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APPLICATION NO. FILING DATE FIRST NAMED INVENTOR ATTORNEY DOCKET NO. CONFIRMATION NO. 08/654,760 05/29/1996 MADHUKAR B. VORA V&F-001 7867

7590 10/01/2003

RONALD CRAIG FISH FALK VESTAL & FISH 16590 OAK VIEW CIRCLE MORGAN HILL, CA 95037 EXAMINER

CRANE, SARA W

ART UNIT PAPER NUMBER

2811

DATE MAILED: 10/01/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

| <i>♣</i> | | | | |
|--|--|--|--|--------------------------|
| | Application No. | - | Applicant(s) | |
| | 08/654,760 | | VORA, MADHUKAR B. | |
| Office Action Summary | Examiner | | Art Unit | |
| | Sara W. Crane | | 2811 | |
| Th MAILING DATE of this communication ap | p ars on the cover s | heet with the c | correspondenc a | nddress |
| Pariod for Renly | | | | |
| A SHORTENED STATUTORY PERIOD FOR REPL THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.º after SIX (6) MONTHS from the mailing date of this communication. If the period for reply specified above is less than thirty (30) days, a rep If NO period for reply is specified above, the maximum statutory period Failure to reply within the set or extended period for reply will, by statut Any reply received by the Office later than three months after the mailin earned patent term adjustment. See 37 CFR 1.704(b). Status | 136(a). In no event, however ly within the statutory minim will apply and will expire SIX | r, may a reply be til um of thirty (30) da K (6) MONTHS fron | mely filed ys will be considered tin n the mailing date of this ED (35 U.S.C. § 133). | nely. communication. |
| 1) Responsive to communication(s) filed on 3/1 | 1 <u>2/02; 23/12/02</u> . | | | |
| 2b)⊠ T | his action is non-fina | al. | | |
| 3) Since this application is in condition for allow closed in accordance with the practice unde | vance except for fon r Ex parte Quayle, 1 | mal matters, _I 1935 C.D. 11, | orosecution as to 453 O.G. 213. | the merits is |
| Disposition of Claims | | | | |
| 4) Claim(s) 1-5 and 7-16 is/are pending in the a | application. | tion | • | |
| 4a) Of the above claim(s) is/are withdr | awn from considera | uon. | | |
| 5) Claim(s) is/are allowed. | | | | |
| 6)⊠ Claim(s) <u>1-5 and 7-16</u> is/are rejected. | | | | |
| 7) Claim(s) is/are objected to. | | 4 | | |
| 8) Claim(s) are subject to restriction and | or election requiren | nent. | | |
| Application Papers | nor | | | |
| 9)☐ The specification is objected to by the Examin | ner. tod or b) Objects | ad to by the Ex | caminer. | |
| 10)☐ The drawing(s) filed on is/are: a)☐ acc Applicant may not request that any objection to | the drawing(s) he held | d in abevance. | See 37 CFR 1.85 | (a). |
| Applicant may not request that any objection to 11) The proposed drawing correction filed on | is: a) annrove | ed b)∏ disapı | oroved by the Exa | miner. |
| 11) The proposed drawing correction filed on | reply to this Office ac | tion. | • | |
| If approved, corrected drawings are required in | Examiner | · ·· | | |
| 12) The oath or declaration is objected to by the | _Adminon | | | |
| Priority under 35 U.S.C. §§ 119 and 120 | oian priority under 26 | 5USC 8 11 | 9(a)-(d) or (f). | |
| 13) Acknowledgment is made of a claim for fore | eigh phonty under o | 0.0.0. | | |
| a) ☐ All b) ☐ Some * c) ☐ None of: | | havid | | |
| 1. Certified copies of the priority docume | d copies of the priority documents have been received. d copies of the priority documents have been received in Application No | | | |
| 2. Certified copies of the priority docum | ents have been rece | ava haan rec | eived in this Natio | onal Stage |
| 3. Copies of the certified copies of the papplication from the International * See the attached detailed Office action for a | list of the certified c | opies not rece | eived. | |
| 14) Acknowledgment is made of a claim for dom | estic priority under 3 | 35 U.S.C. § 1 | 19(e) (to a provis | ional application). |
| a) ☐ The translation of the foreign language 15) ☐ Acknowledgment is made of a claim for dom | nrovisional applicat | ion has been | received. | |
| 1 | | | | |
| Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449) Paper No | 4)) 5) (s) 6) | Notice of Infor | mary (PTO-413) Par mal Patent Applicatio | er No(s) on (PTO-152) |

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DETAILED ACTION

Specification

The amendments to the specification filed 3 December 2002 is objected to under 35 U.S.C. 132 because it introduces new matter into the disclosure. 35 U.S.C. 132 states that no amendment shall introduce new matter into the disclosure of the invention. The added material which is not supported by the original disclosure is as follows:

Page 8, line 11-12, addition of wells 62 and 64 to form an EEPROM device.

Page 8, line 24, the 300 angstrom thick grown oxide layer.

Page 10, line 10, the etch being vertically down, or vertical etch.

Page 10, lines 20-22, change of "gate windows" to --wells-- and the layer covering "the entire horizontal top surface of the substrate extending laterally in all directions."

Page 10, lines 23-24, the nitride layer having all portions being removed on horizontal surfaces.

Page 10, last 2 lines, to page 11, first line. The entire sentence beginning with "Next, a layer of oxide insulator "

Page 11, lines 3-4, nitride layer removed from vertical walls of wells 88 and 90.

Page 11, lines 6-7, gate oxide grown "on exposed silicon surfaces including ther vertical walls of the wells 88 and 90"

Page 11, line 8, "doped substrate" layers.

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Page 11, lines 17-19, the phrase beginning with "and are self aligned . . ." and ending with "at the bottoms of the wells 88 and 90."

Page 12, lines 11-12, the wells "of the NMOS and PMOS devices."

Page 12, line 14, "over the EEPROM device.

Page 13, line 8, the "vertical" sidewalls.

Page 13, line 19, the designation of layer 86 as "drain."

Page 14, lines 8-9, the P well "of the NMOS device."

Page 14, lines 12- 16, the sentence beginning with "Next, the photoresist is removed . . ." and ending with "for the NMOS device."

All added material to the "Process Flow" presented in chart form on pages 15-20. Each added limitation either changes the scope of the teaching, or makes specific changes to details of the process itself which do not correspond to the original teaching of the specification.

Applicant is required to cancel the new matter in the reply to this Office Action.

Examiner notes that changes to the specification of the scope presented in this amendment are typically presented as a continuation-in-part application.

Claim Rejections - 35 USC § 112

Claims 1-5 and 7-16 are rejected under 35 U.S.C. 112, first paragraph, as failing to comply with the written description requirement. The claim(s) contains subject matter which was not described in the specification in such a way as to reasonably convey to

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one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention.

Each of claims 2, 7, 10, and 15 recites a "self-aligned" floating gate which is formed "without using any critical mask" and where a "critical mask" is a mask "which requires close alignment to registration marks so as to cause close alignment between different structures on an integrated circuit." The specification does not say anything at all about forming a "self-aligned" floating gate, and no "critical mask" or lack thereof is described anywhere in the specification. The only thing the specification says about the formation of the floating gate is the sentence spanning pages 9 and 10, which says, "To form the floating gate, the doped polysilicon is etched back off all horizontal surfaces and part way down into the recess gate windows" The specification does not say anything about whether or not a mask is used, much less whether or not such a mask is "critical." Moreover, no "self-aligned" floating gate is taught anywhere in the specification. The word "self-aligned" is used only to describe the memory cell, as in the heading of the table on page 13.

Claim 1 is included in the rejection because the remarks of 23 December 2003, page 16 et seq., discuss the meaning of the claim term "self aligned" (used in claim 1) in terms of the "critical mask" noted above. This interpretation of "self aligned" as applied to the floating gate of claim 1 would mean that claim 1 also encompasses new matter.

The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

Claims 1-5 and 7-16 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

The meaning of the term "self aligned" is not clear. The Board decision of 26 September 2001 appears to set forth a specific definition of this term. (I.e., a "self-aligned" floating age "will not have any horizontal component on the surface of the substrate or on the bottom of the well and therefore will not extend beyond the perimeter of the trench.") Applicant now argues that "self aligned" is defined in terms of a process of making, which has no "critical mask." Such a definition is considerably broader than that adopted by the Board decision. Because the specification does not refer to any process of making the floating gate, defining the term "self aligned" in terms of a process of making lacks clarity.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to S. Crane, whose telephone number is (703) 308-4894.

The fax phone number for this Group is (703) 308-7722.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the Group receptionist, whose telephone number is (703) 308-0956.

Sara W. Crane Primary Examiner Art Unit 2811